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TATES PATENT AND TRADEMARK OFFICE

1991-99

In re Application of:

MARK I. GARDNER MARK C. GILMER

Examiner: A. Mai

Serial No.: 09/079,759

Group Art Unit: 2814

Filed: May 15, 1998

Att'y Docket: 2000.002600/TT2587

For: METHOD OF MAKING AN

ADVANCED ISOLATION

STRUCTURE FOR HIGH DENSITY SEMICONDUCTOR DEVICES

(as amended)

AUG 30 1999

## RESPONSE TO OFFICE ACTION DATED JUNE 23, 1999

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## **BOX AF**

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

## CERTIFICATE OF MAILING

I hereby certify that this paper or fee is being deposited with the United States Postal Service with sufficient postage as "FIRST CLASS MAIL" addressed to: Assistant Commissioner for Patents, Washington, DC 20231, this 23rd day of August, 1999.

Ende Muhart
Signature

This paper is submitted in response to the Office Action dated June 23, 1999 for which the date for response is September 23, 1999. Therefore, this response is filed within **two months** of the mailing date of the Office Action dated June 23, 1999.

## IN THE CLAIMS

Please amend claims 20 and 28 as follows:

20. (Twice amended) A method for forming an isolation trench in a semiconductor substrate, said substrate having a surface, the method comprising:

forming a first recess in said substrate, said first recess having a first width of at most about 2500 [3000] Å and extending a first depth beneath the surface of said substrate;